

CIR-V3DASI1604G

DDR3 Registered DIMM 1600MHz 4GB

Description

CIR-V3DASI1604G is a high speed 4GB DDR3L-1600 Registered ECC. It is designed for mission critical application memory solution. This DIMM includes Error Checking and Correcting (ECC) for maximum reliability. The modules is constructed using 256Mx8 SDRAMs, and is fully compliant with JEDEC specifications. Decoupling capacitors are mounted on the PCB board for better signal integrity. The DIMM feature serial presence detect (SPD) based on a serial EEPROM device using the 2-pin I2C protocol.

Specifications

Density	4GB
Pin Count	240pin
Type	Registered
Dimensions	133.35mm x 30.0mm
ECC	With ECC
Component Config	256M x 8 bit
Data Rate	1600 MHz
CAS Latency	11
Voltage	1.5V / 1.35V
PCB Layers	6
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Dual Rank

Features

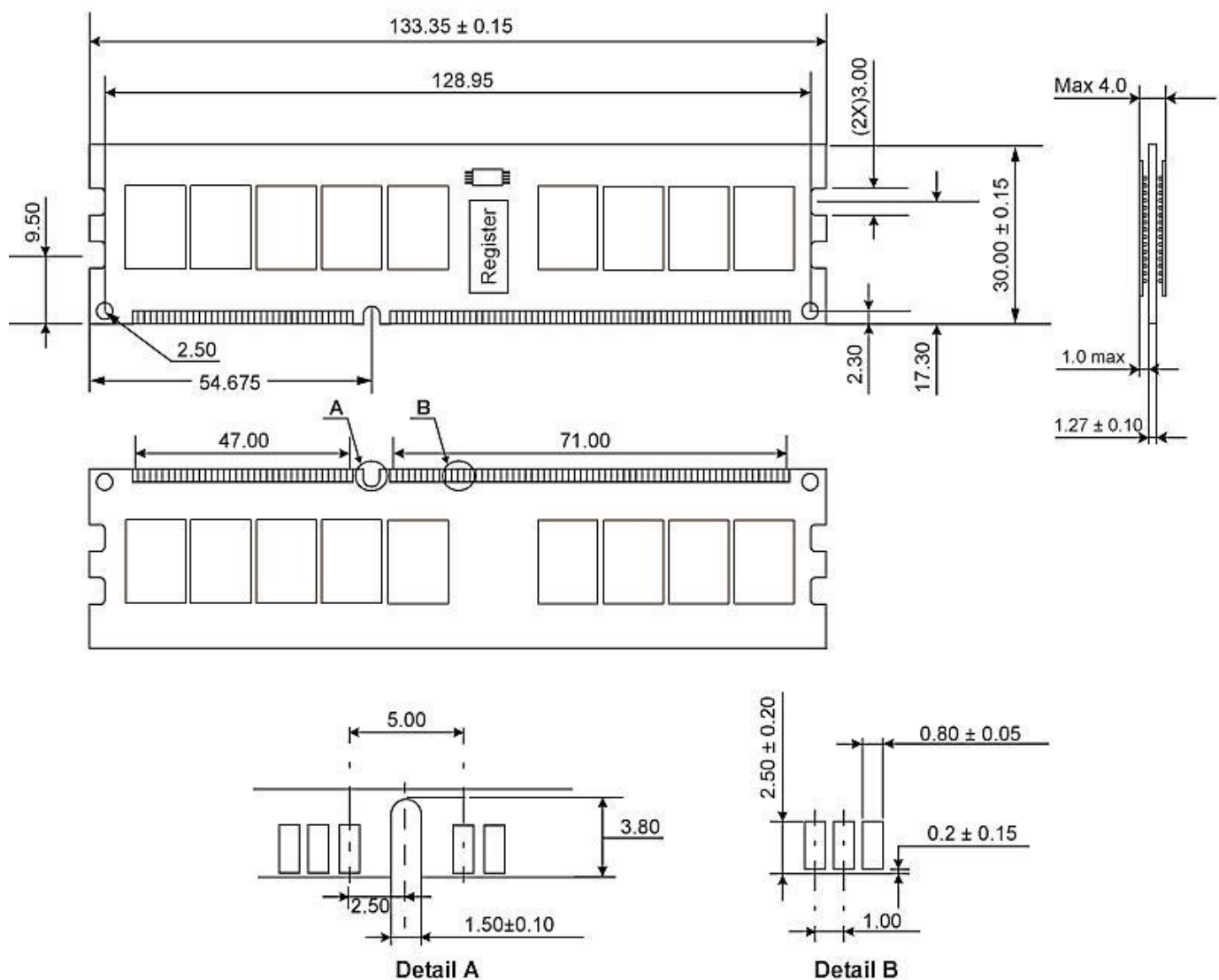
- 240-pin Registered Dual Inline Memory Module (RDIMM)
- Memory Module Organization 512Mx72
- Power Supply: VDD= 1.5V (1.425V to 1.575V) & VDD= 1.35V (1.283V to 1.45V)
- CAS (READ) latency (CL): 6, 7, 8, 9, 10, 11
- Bi-Directional Differential Data Strobe
- Eight Internal banks for concurrent operation (components)
- Refresh: Auto-refresh, self-refresh
- Burst Length (BL) switch on-the-fly BL8 or BC4(Burst Chop)
- Supports ECC error correction and detection
- On-Die-Termination (ODT) for better signal quality
- RoHS Compliant (Lead Free) Memory module
- Average Refresh Period 7.8us at lower than a TCASE 85°C, 3.9us at 85°C < TCASE < 95 °C

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support						CL-tRCD-tRP
		CL6	CL7	CL8	CL9	CL10	CL11	
DDR3-1600	PC3-12800	800	1066	1066	1333	1333	1600	11-11-11

Package Dimensions

Unit: mm



Tolerances : ± 0.15 mm unless otherwise specified